

	Hits	Search Text	DBs	Time Stamp
1	2	"6682981".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 17:34
2	2	"5869354".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 16:19
3	2	"5354695".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 16:21
4	2	"5451489".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 16:30
5	2	"6288561".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 16:31
6	2	"5985693".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 16:34
7	1187	stress near2 (layer membrane) with (device or devices)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/26 20:04

	Hits	Search Text	DBs	Time Stamp
8	68	stress near2 (layer membrane) with (device or devices) same substrate same circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 17:36
9	84	("2915722" "3202948" "3559282" "3560364" "3602982" "3716429" "3777227" "3868565" "4070230" "4131985" "4142004" "4262631" "4394401" "4401986" "4416054" "4539068" "4585991" "4612083" "4617160" "4618397" "4618763" "4663559" "4693770" "4702336" "4702936" "4706166" "4721938" "4761681" "4784721" "4810673" "4825277" "4857481" "4924589" "4950987" "4952446" "4957882" "4966663" "5008619" "5010024" "5070026" "5071510" "5098865" "5110373" "5130894" "5132244" "5156909" "5203731" "5236118" "5240458" "5262351" "5273940" "5274270" "5279865" "5284796" "5358909" "5363021" "5385632" "5424920" "5426072" "5426363" "5432444" "5432729" "5434500" "5457879" "5502667" "5534465" "5580687" "5581498" "5583688" "5637536" "5750211" "5760478" "5793115" "5856695" "5868949" "5870176" "5882532" "6045625" "6084284" "RE34893") .PN.	US-PGPUB; USPAT; USOCR	2004/11/17 17:55
10	0	("6682981") .URPN.	USPAT	2004/11/17 17:59
11	8	("4070230" "4131985" "4618397" "4702936" "4721938" "4952446" "5071510" "5110373") .PN.	US-PGPUB; USPAT; USOCR	2004/12/11 22:31
12	19	("5354695") .URPN.	USPAT	2004/11/17 18:00

	Hits	Search Text	DBs	Time Stamp
13	6	("4924589" "5420458" "4825277").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/17 18:11
14	13	("4966663").URPN.	USPAT	2004/11/26 19:53
15	99	stress near2 (layer membrane) with dynes	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/26 20:09
16	1	stress near2 (layer membrane) with fracture with dynes	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/26 20:10
17	111	stress near2 (layer membrane) with fracture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:02

	Hits	Search Text	DBs	Time Stamp
18	51	US-Re34893-\$.DID. OR US-2915722- \$.DID. OR US-3202948-\$.DID. OR US- 3559282-\$.DID. OR US-3560364-\$.DID. OR US-3602982-\$.DID. OR US-3615901- \$.DID. OR US-3716429-\$.DID. OR US- 3777227-\$.DID. OR US-3868565-\$.DID. OR US-3922705-\$.DID. OR US-3997381- \$.DID. OR US-4070230-\$.DID. OR US- 4131985-\$.DID. OR US-4142004-\$.DID. OR US-4251909-\$.DID. OR US-4262631- \$.DID. OR US-4394401-\$.DID. OR US- 4401986-\$.DID. OR US-4416054-\$.DID. OR US-4539068-\$.DID. OR US-4585991- \$.DID. OR US-4612083-\$.DID. OR US- 4617160-\$.DID. OR US-4618397-\$.DID. OR US-4618763-\$.DID. OR US-4663559- \$.DID. OR US-4684436-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:30

	Hits	Search Text	DBs	Time Stamp
19	58	US-4702336-\$.DID. OR US-4702936- \$.DID. OR US-4706166-\$.DID. OR US- 4721938-\$.DID. OR US-4761681-\$.DID. OR US-4784721-\$.DID. OR US-4810673- \$.DID. OR US-4825277-\$.DID. OR US- 4857481-\$.DID. OR US-4924589-\$.DID. OR US-4940916-\$.DID. OR US-4950987- \$.DID. OR US-4952446-\$.DID. OR US- 4954865-\$.DID. OR US-4957882-\$.DID. OR US-4965415-\$.DID. OR US-4966663- \$.DID. OR US-4994735-\$.DID. OR US- 5008619-\$.DID. OR US-5010024-\$.DID. OR US-5020219-\$.DID. OR US-5034685- \$.DID. OR US-5070026-\$.DID. OR US- 5071510-\$.DID. OR US-5098865-\$.DID. OR US-5103557-\$.DID. OR US-0510373- \$.DID. OR US-5111278-\$.DID. OR US- 5116777-\$.DID. OR US-5130894-\$.DID. OR US-5132244-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:31

	Hits	Search Text	DBs	Time Stamp
20	61	US-5151775-\$.DID. OR US-5156909- \$.DID. OR US-5203731-\$.DID. OR US- 5225771-\$.DID. OR US-0523618-\$.DID. OR US-5262351-\$.DID. OR US-5270261- \$.DID. OR US-5273940-\$.DID. OR US- 5274270-\$.DID. OR US-5279865-\$.DID. OR US-5284796-\$.DID. OR US-5323035- \$.DID. OR US-5324687-\$.DID. OR US- 5354695-\$.DID. OR US-5363021-\$.DID. OR US-5385632-\$.DID. OR US-5385909- \$.DID. OR US-5420458-\$.DID. OR US- 5424920-\$.DID. OR US-5426072-\$.DID. OR US-5426363-\$.DID. OR US-5432444- \$.DID. OR US-5432729-\$.DID. OR US- 5434500-\$.DID. OR US-5451489-\$.DID. OR US-5453404-\$.DID. OR US-5457879- \$.DID. OR US-5476813-\$.DID. OR US- 5489554-\$.DID. OR US-5502667-\$.DID. OR US-5512397-\$.DID. OR US-5527645- \$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:31

	Hits	Search Text	DBs	Time Stamp
21	52	US-5529829-\$.DID. OR US-5534465- \$.DID. OR US-5555212-\$.DID. OR US- 5563084-\$.DID. OR US-5571741-\$.DID. OR US-5580687-\$.DID. OR US-5581498- \$.DID. OR US-5582939-\$.DID. OR US- 5583688-\$.DID. OR US-5592007-\$.DID. OR US-5592018-\$.DID. OR US-5595933- \$.DID. OR US-5606186-\$.DID. OR US- 5627112-\$.DID. OR US-5629137-\$.DID. OR US-5633209-\$.DID. OR US-5637536- \$.DID. OR US-5654127-\$.DID. OR US- 5654220-\$.DID. OR US-5656552-\$.DID. OR US-5675185-\$.DID. OR US-5694588- \$.DID. OR US-5725995-\$.DID. OR US- 0575021-\$.DID. OR US-5760478-\$.DID. OR US-5773152-\$.DID. OR US-5786116- \$.DID. OR US-5793115-\$.DID. OR US- 5831280-\$.DID. OR US-5834334-\$.DID. OR US-5840593-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:32

	Hits	Search Text	DBs	Time Stamp
22	38	US-5868949-\$.DID. OR US-5869354-\$.DID. OR US-5870176-\$.DID. OR US-5880010-\$.DID. OR US-5882532-\$.DID. OR US-5902118-\$.DID. OR US-5915167-\$.DID. OR US-5946559-\$.DID. OR US-5985693-\$.DID. OR US-5998069-\$.DID. OR US-6008126-\$.DID. OR US-6020257-\$.DID. OR US-6045625-\$.DID. OR US-6084284-\$.DID. OR US-6097096-\$.DID. OR US-6133640-\$.DID. OR US-6194245-\$.DID. OR US-6197456-\$.DID. OR US-6208545-\$.DID. OR US-6236602-\$.DID. OR US-6261728-\$.DID. OR US-6288561-\$.DID. OR US-6294909-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:33
23	8	S23 and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:40
24	20	S24 and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 22:43
25	15	S25 and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:42

	Hits	Search Text	DBs	Time Stamp
26	17	S26 and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:42
27	17	S27 and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 21:43
28	439	stress near2 (layer membrane) with circuit\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:12
29	1289	data adj sink and data adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:17
30	854	data adj sink same data adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:13
31	142	data adj sink same data adj source and interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:15
32	1	data adj sink same data adj source and interconnect and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:14

	Hits	Search Text	DBs	Time Stamp
33	1	data adj sink same data adj source and interconnect and (etch etching etched) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:15
34	8	data adj sink same data adj source same interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:15
35	34	data adj sink same data adj source and interconnect and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:16
36	69	data adj sink and data adj source and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:26
37	184	data adj sink and data adj source and interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:30
38	35	data adj sink and data adj source and interconnect and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/10 22:30
39	320	stress with (deposit depositing deposited) with ((chemical adj vapor) or (RF near2 energy))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 20:38

	Hits	Search Text	DBs	Time Stamp
40	86	stress near5 (deposit depositing deposited) near5 ((chemical adj vapor) or (RF near2 energy))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 20:39
41	9862	interconnect and substrate near5 (etch etching etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 22:29
42	2340	interconnect and substrate near5 (etch etching etched) and stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 22:30
43	1210	interconnect and substrate near5 (etch etching etched) and stress with (layer membrane film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 22:34
44	626	interconnect and substrate near5 (etch etching etched) and stress with (layer membrane film) and (stack stacking stacked)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/11 22:34
45	135	438/6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22
46	3720	438/17.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22

	Hits	Search Text	DBs	Time Stamp
47	596	438/53.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22
48	329	438/406.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22
49	138	438/411.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22
50	949	438/479.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22
51	511	438/626.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/12 22:22
52	326	stress near2 dielectric near2 (layer membrane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/30 15:20
53	270	stress near2 dielectric near2 (layer membrane) and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/30 15:20

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54	108	stress near2 dielectric near2 (layer membrane) and circuit same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/30 15:20
55	149	elastic near2 dielectric near2 (layer membrane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/30 15:20
56	55	elastic near2 dielectric near2 (layer membrane) and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/30 15:20
57	16	elastic near2 dielectric near2 (layer membrane) and circuit same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/30 15:21
58	33	("4500905" "4835765" "4892753" "4897708" "4919749" "4939568" "4983251" "5000113" "5144142" "5240458" "5259247" "5262341" "6087264" "6230233" "6445006" "6518073" "6682981" "6713327") .pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/28 20:37
59	2	"4934799" .pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/25 13:09
60	275	(stress and dielectric and circuit and substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/25 14:46

	Hits	Search Text	DBs	Time Stamp
61	104	(stress with dielectric with (layer membrane) and circuit and substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/25 14:46
62	21	(stress with dielectric with (layer membrane) with circuit and substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/25 14:46
63	115	(stress and dielectric and circuit and substrate).clm.	US-PGPUB	2005/08/25 14:46
64	56	(stress with dielectric with (layer membrane) and circuit and substrate).clm.	US-PGPUB	2005/08/25 14:47
65	16	(stress with dielectric with (layer membrane) with circuit and substrate).clm.	US-PGPUB	2005/08/25 14:47
66	5	("5354695" "5869354" "5985693" "6682981").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/10/27 14:59
67	35	("3636358" "4566037" "4622632" "5245227" "5283107" "5293467" "5399505" "5450603" "5572689" "6092174" "6154809" "6300935" "6301653" "6320593" "6894392" "5062689").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/05/04 10:27
68	2	"20050023656"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/05/04 10:30
69	47	"5117282"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/05/24 17:37

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70	0	"5117282.pn."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/05/24 17:37
71	2	"5117282".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/05/24 17:37
72	2	"4735702".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/12 11:41
73	2	"20050176174"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:41
74	37189	silicon adj (dioxide nitride) with dielectric and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:28
75	8177	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:20
76	165	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (circuit circuitry) with active with source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 10:58

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77	2413	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:21
78	1	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and (interconnect interconnection) with data adj source with data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:26
79	1	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and (interconnect interconnection) same data adj source with data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:24
80	1	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and (interconnect interconnection) same data adj source same data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:24
81	1	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and data adj source same data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:25
82	1	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and data adj source and data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:25

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83	1	silicon adj (dioxide nitride) with dielectric and substrate and data adj source and data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:25
84	100	substrate and data adj source and data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:25
85	2	dielectric and substrate and data adj source and data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:25
86	2	substrate and (interconnect interconnection) with data adj source with data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:27
87	2	substrate and (interconnect interconnection) same data adj source with data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:27
88	2	substrate and (interconnect interconnection) same data adj source same data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:27
89	36	substrate and (interconnect interconnection) and data adj source same data adj sink	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:27

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90	19374	silicon adj (dioxide nitride) with dielectric and substrate and substrate with (remove removing removed etch etching etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:36
91	4279	silicon adj (dioxide nitride) with dielectric and substrate and substrate with (remove removing removed etch etching etched) and dielectric with (circuit circuitry)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:30
92	85	silicon adj (dioxide nitride) with dielectric and substrate and substrate with (remove removing removed etch etching etched) and dielectric with (circuit circuitry) and (circuit circuitry) with active with source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:30
93	55	silicon adj (dioxide nitride) with dielectric and substrate and substrate near3 (remove removing removed etch etching etched) and dielectric with (circuit circuitry) and (circuit circuitry) with active with source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:30
94	29	silicon adj (dioxide nitride) with dielectric and substrate and substrate near (remove removing removed etch etching etched) and dielectric with (circuit circuitry) and (circuit circuitry) with active with source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:32
95	29	silicon adj (dioxide nitride) with dielectric and substrate near (remove removing removed etch etching etched) and dielectric with (circuit circuitry) and (circuit circuitry) with active with source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:32

	Hits	Search Text	DBs	Time Stamp
96	7620	silicon adj (dioxide nitride) with dielectric and substrate and substrate with (remove removing removed etch etching etched) with (back backside second under beneath)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:34
97	1677	silicon adj (dioxide nitride) with dielectric and substrate and substrate near3 (remove removing removed etch etching etched) near3 (back backside second under beneath)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:34
98	362	silicon adj (dioxide nitride) with dielectric and substrate and substrate near3 (remove removing removed etch etching etched) near3 (back backside second under beneath) and dielectric with (circuit circuitry)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:35
99	111	silicon adj (dioxide nitride) with dielectric and substrate and substrate near3 (remove removing removed etch etching etched) near3 (back backside second under beneath) and dielectric with (circuit circuitry) and (circuit circuitry) with active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:35
100	111	silicon adj (dioxide nitride) with dielectric and substrate near3 (remove removing removed etch etching etched) near3 (back backside second under beneath) and dielectric with (circuit circuitry) and (circuit circuitry) with active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:35
101	23309	silicon adj (dioxide nitride) with dielectric and substrate and substrate with (thin thinning thinning thinned remove removing removed etch etching etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:37

	Hits	Search Text	DBs	Time Stamp
102	3026	silicon adj (dioxide nitride) with dielectric and substrate and substrate near3 (thin thinning thinning thinned remove removing removed etch etching etched) and dielectric with (circuit circuitry)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:37
103	409	silicon adj (dioxide nitride) with dielectric and substrate and substrate near3 (thin thinning thinning thinned remove removing removed etch etching etched) near3 (back backside second under beneath) and dielectric with (circuit circuitry)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:37
104	80	("2915722" "3202948" "3559282" "3560364" "3602982" "3716429" "3777227" "3868565" "4070230" "4131985" "4142004" "4262631" "4394401" "4401986" "4416054" "4539068" "4585991" "4612083" "4617160" "4618397" "4618763" "4663559" "4693770" "4702936" "4706166" "4721938" "4761681" "4784721" "4810673" "4857481" "4924589" "4950987" "4952446" "4957882" "5008619" "5010024" "5070026" "5071510" "5098865" "5110373" "5130894" "5132244" "5156909" "5203731" "5236118" "5262351" "5273940" "5274270" "5279865" "5284796" "5358909" "5363021" "5385632" "5424920" "5426072" "5426363" "5432444" "5432729" "5434500" "5457879" "5502667" "5534465" "5580687" "5581498" "5583688" "5637536" "5750211" "5760478" "5793115" "5856695" "5868949" "5870176" "5882532" "6045625" "6084284" "RE34893") .PN.	US-PGPUB; USPAT; USOCR	2006/06/15 18:40

	Hits	Search Text	DBs	Time Stamp
105	198	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and (interconnect interconnection) with (transfer transferring transferred transfered information data)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:58
106	100	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (interconnect interconnection) with dielectric and (interconnect interconnection) near3 (transfer transferring transferred transfered information data)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/15 18:59
107	1611	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (circuit circuitry) with active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 10:58
108	473	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (circuit circuitry) with active and (interconnect interconnection) with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 11:18
109	36	silicon adj (dioxide nitride) with dielectric and substrate and dielectric with (circuit circuitry) and (circuit circuitry) with active and (interconnect interconnection) with dielectric and @ay<"1993"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 11:18
110	0	leedy.in. and perkins-pamela.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 13:08

	Hits	Search Text	DBs	Time Stamp
111	0	leedy.in. and perkins.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 13:08
112	156	leedy.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 13:09
113	8	leedy-glenn.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 13:09
114	2	"5188706".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 14:31
115	16490	(flexible elastic) near (circuit circuitry)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 19:59
116	7398	(flexible elastic) near (circuit circuitry) and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 19:59
117	2339	(flexible elastic) near (circuit circuitry) and substrate and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 19:59

	Hits	Search Text	DBs	Time Stamp
118	380	(flexible elastic) near (circuit circuitry) and substrate and dielectric and @ay<"1993"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:09
119	7	(flexible elastic) near (circuit circuitry) and substrate and dielectric and @ay<"1993" and dielectric with silicon adj (dioxide nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:02
120	7	(flexible elastic) near (circuit circuitry) and substrate and dielectric and @ay<"1993" and dielectric with silicon adj (dioxide oixde nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:02
121	7	(flexible elastic) near (circuit circuitry) and substrate and dielectric and @ay<"1993" and dielectric with silicon adj (dioxide oxide nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:03
122	14	(flexible elastic) near (circuit circuitry) and substrate and dielectric and @ay<"1993" and dielectric with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:04
123	0	(flexible elastic) near (circuit circuitry) near intergated and substrate and dielectric and @ay<"1993" and dielectric with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:04
124	2	(flexible elastic) near (circuit circuitry) near integrated and substrate and dielectric and @ay<"1993" and dielectric with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:05

	Hits	Search Text	DBs	Time Stamp
125	7	(flexible elastic) near (circuit circuitry) near integrated and substrate and dielectric and @ay<"1993"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:05
126	312	(flexible elastic) near (circuit circuitry) and substrate and dielectric and @ay<"1992"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:09
127	282	(flexible elastic) adj (circuit circuitry) and substrate and dielectric and @ay<"1992"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/06/16 20:09